



04-02-03

2829

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April 30, 2003

Box: Non-Fee Amendment
Commissioner For Patents
Washington, D.C. 20231

Re: Applicant(s): Michael R. Krames; Tetsuya Takeuchi; Norihide Yamada; Hiroshi
Amano; Isamu Akasaki
Assignee: Lumileds Lighting U.S., LLC
Title: Nitride Semiconductor Device With Reduced Polarization Fields
Serial No.: 09/992,192
Examiner: Maria F. Guerrero
Docket No.: M-11040-3P US
Filed: November 13, 2001
Group Art Unit: 2822

Dear Sir:

Transmitted herewith are the following documents in the above-identified application:

- (1) This Transmittal Letter (1 page);
- (2) Response to Office Action (9 pages).

- ☒ No additional fee is required.
☐ The fee has been calculated as shown below:

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	Claims Remaining <u>After Amendment</u>		Highest No. Previously <u>Paid For</u>		Present <u>Extra</u>	<u>Rate</u>		Additional <u>Fee</u>
Total Claims	18	Minus	23	=	0	x \$18	\$	0.00
Independent Claims	3	Minus	4	=	0	x \$84	\$	0.00
<input type="checkbox"/>	Fee of _____ for the first filing of one or more multiple dependent claims per application						\$	
<input checked="" type="checkbox"/>	Conditional Petition for Extension of Time: If an extension of time is required for timely filing of the enclosed document(s) after all papers filed with this transmittal have been considered, an extension of time is hereby requested.							
<input type="checkbox"/>	Please charge our Deposit Account No. 502226 in the amount of							0.00
<input checked="" type="checkbox"/>	Also, charge any additional fees required and credit any overpayment to our Deposit Account No. 502226.							
Total:							\$	0.00

EXPRESS MAIL LABEL NO:

EV 342554919 US

Respectfully submitted,

R. Leiterman
Rachel V. Leiterman
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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

#9/A
1/20/03

Applicants: Michael R. Krames; Tetsuya Takeuchi; Norihide Yamada; Hiroshi Amano; Isamu Akasaki
Assignee: Lumileds Lighting U.S. LLC
Title: Nitride Semiconductor Device With Reduced Polarization Fields
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San Jose, California
April 30, 2003

COMMISSIONER FOR PATENTS
Washington, D. C. 20231

RESPONSE TO OFFICE ACTION

Dear Sir:

This responds to the Office Action dated January 31, 2003. Please amend the above-identified application as follows.

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IN THE CLAIMS

No claims are amended in this submission. The claims are reproduced below for the Examiner's convenience.

1. A method for fabricating a light-emitting semiconductor device including a III-Nitride quantum well layer, said method comprising:
selecting a facet orientation of said III-Nitride quantum well layer to control a field strength of a piezoelectric field therein; and
growing said III-Nitride quantum well layer with said selected facet orientation.
2. The method of Claim 1, further comprising selecting said facet orientation to reduce a magnitude of an electric field strength in said quantum well layer.